

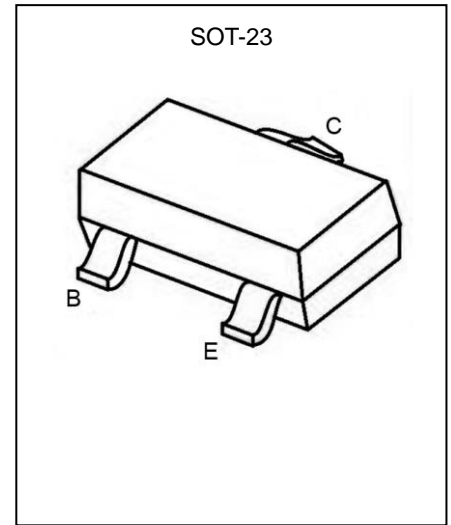


**2SA1037 Transistor(PNP)**

**Feature**

- Excellent  $h_{FE}$  linearity
- Complementary NPN Type Available(2SC2412)

Rank	Q	R	S
Range	120~270	180~390	270~560
Marking	FQ	FR	FS



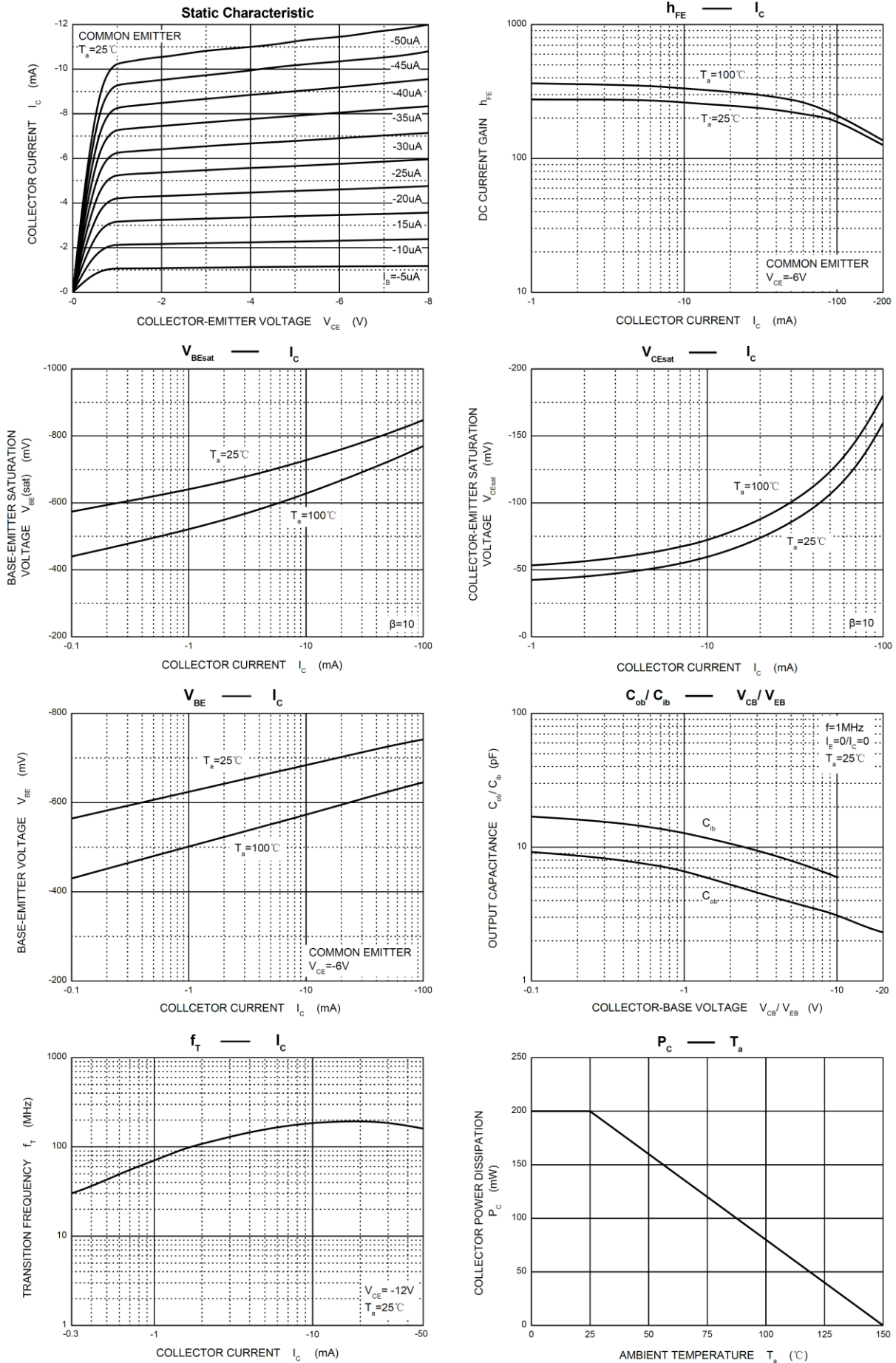
**MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-60	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-6	V
Collector Current -Continuous	$I_c$	-0.1	A
Power Dissipation	$P_d$	0.2	W
Junction Temperature	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^{\circ}\text{C}$

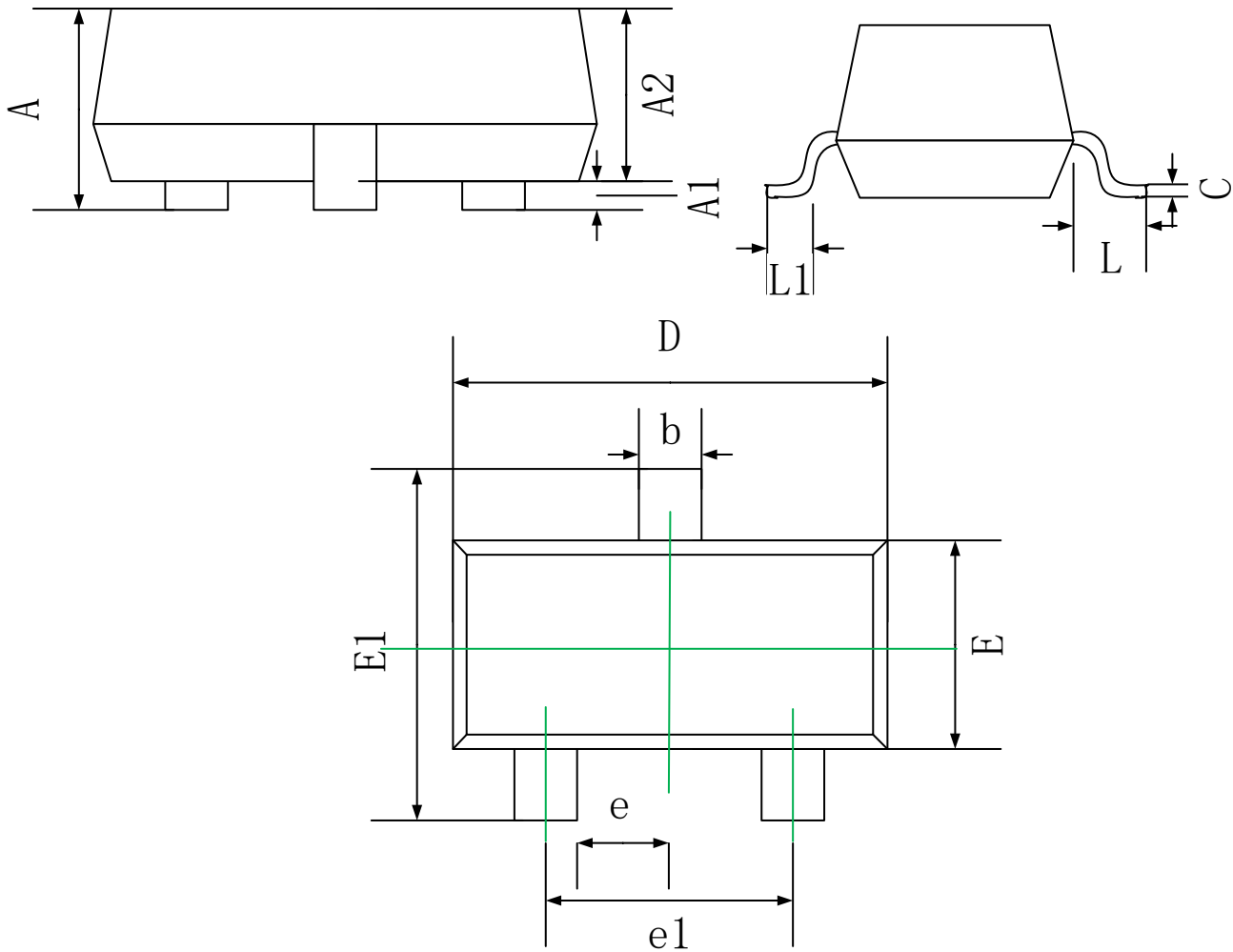
**ELECTRICAL CHARACTERISTICS( $T_a=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-50\mu\text{A}, I_E=0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-1\text{mA}, I_B=0$	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-6		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-60\text{V}, I_E=0$		-100	nA
Emitter cut-off current	$I_{CEO}$	$V_{CE}=-6\text{V}, I_C=0$		-100	nA
DC current gain	$h_{FE}$	$V_{CE}=-6\text{V}, I_C=-10\text{mA}$	120	560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=-50\text{mA}, I_B=-5\text{mA}$		-0.5	V
Output Capacitance	$C_{OB}$	$V_{CB}=-12\text{V}, f=1.0\text{MHz}, I_E=0$		4.0 5.0	pf
Transition frequency	$f_T$	$V_{CE}=-12\text{V}, I_c=-2\text{mA}, f=12\text{MHz}$		180	MHZ

**Typical Characteristics**



## SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50